MarlinTPC Simulation and Digitisation Current Developments for my CLIC Detector Study

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MarlinTPC EVO Meeting

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Geant4 / Mokka

- SimTrackerHit with the deposited energy in GeV
- One primary electron corresponds to 26 eV

PrimaryIonisationProcessor

- One SimTrackerHit per primary electron, even if they are created at the same space point
- Energy information in SimTrackerHit was not used

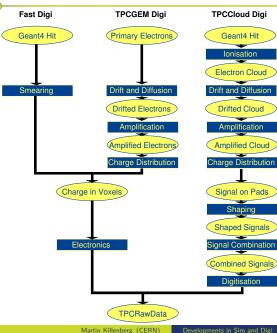
New:

- Energy is 26 eV per electron
- Electrons at the same space point can be grouped to one hit (optional)
- \Rightarrow Output compatible with Mokka output
 - TPCGEM digi currently still expects one hit per electron (to be fixed)





Digitisation Overview



Fast Digi

- Only two steps from input to raw data
- Map of voxels (3D space buckets) implements pile-up
 - of several hits in the event
 - of events in a bunch train (not implemented yet)
 - of background (not implemented yet)

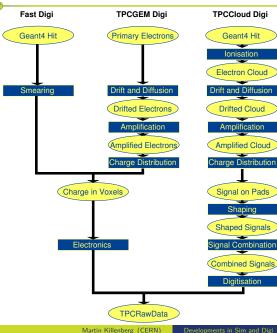
TPCGEM Digi

- Track every single electron
- Also uses the voxel map and the same electronics than Fast Digi

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Digitisation Overview



TPCCloud Digi

- Uses clouds instead of single electrons (faster)
- Does not use a global voxel map
- Used in Likelihood fitter

Remarks:

- TPCGEM Digi and TPCCloud Digi are very similar ⇒ Can we use parts of the same code in both?
- In the following I will only show the fast branch which I use in my study

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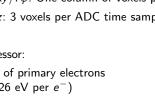
MokkaToVoxelProcessor

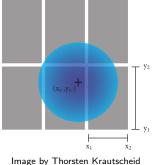
The voxel map:

- Segmentation in $xy/r\varphi$: One column of voxels per pad
- Segmentation in z: 3 voxels per ADC time sample (processor parameter)

The steps in this processor:

- Calculate number of primary electrons from Mokka hit (26 eV per e^-)
- Apply gas gain (currently without fluctuations)
- Distribute charge according to diffusion: ChargeDistributor helper class from **TPCGEM** Digi
 - Calculate number of electrons per pad with Gaussian distribution ($\sigma_{\rm trans}$)
 - Calculate number of electrons per time bin with Gaussian distribution (σ_{long})







Changes¹ in MokkaToVoxelProcessor

Position of readout anode (zAnode)

- In Mokka: 5 mm air gap at z=0
- Drift distance alone is not sufficient information
- zAnode currently user parameter in GEAR file

Two half TPCs

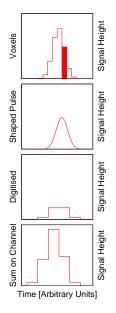
- Current solution (quick hack): Have two voxel maps and write two collection
- All following processors have to be called twice
- Correct solution: Use different modules for each end cap
 - Voxel map has to be extended with module index (automatically introduced multi module capability per end plate)
 - Each module has to have a z position (extend GEAR?)
 - GEAR multi module information has to be merged into XML file from MOKKA

¹not in the trunk yet





TPCElectronicsProcessor



The TPCElectronicsProcessor simulates n bit FADC

(e. g. ALTRO readout with 10 bit 40 MHz ADCs)

Old version:

- Calculate CoG of the voxel signal
- Apply Gaussian shaping around CoG and digitise
- Adjustable cutoff of trailing edge (asymmetric shape)
- Electronics threshold
- Bad performance in case of overlapping pulses

New version:

- For the charge **in each voxel** a Gaussian shaping is applied
- The shaped signal is digitised
- The digitised signals for one channel are summed up
- + Realistic signal for overlapping pulses
- No asymmetry and threshold yet



- The current digitisation does not introduce pedestals and noise
- Reconstruction needs noise levels
- $\Rightarrow\,$ Helper processor which just writes 0 to both pedestal and pedestal width

Remarks:

- The empty pedestals collection uses 500 MB of memory (for an LDC type end plate)
- Pedestal subtraction is usually handled already on front end electronics
- Do we need an individual noise level for each channel? If not, we could have a reco which does not require the huge collection (but can use it if provided)

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